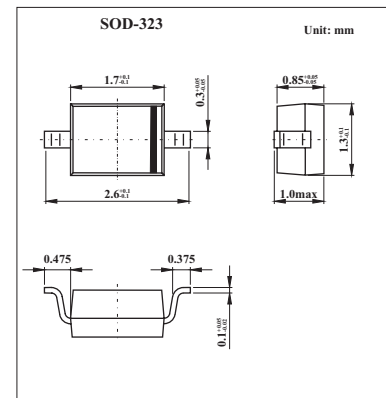


## Silicon Epitaxial Planar Pin Diode

## HVU132

## ■ Features

- Low capacitance. (C=1.0pF max)
- Low forward resistance. ( $r_f=0.7\ \Omega$  max)

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}$	65	V
Reverse voltage	$V_R$	60	V
Forward current	$I_F$	100	mA
Power dissipation	$P_d$	150	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	$I_R$	$V_R = 60\text{ V}$			0.1	nA
Forward voltage	$V_F$	$I_F = 10\text{ mA}$			1.0	V
Capacitance	C	$V_R = 1\text{ V}, f = 1\text{ MHz}$			0.5	pF
Forward resistance	$r_f$	$I_F = 10\text{ mA}, f = 100\text{ MHz}$			2.0	$\Omega$

## ■ Marking

Marking	P2